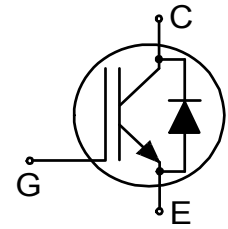


TRENCHSTOP™ IGBT6

IGBT in trench and field-stop technology with soft, fast recovery anti-parallel Rapid diode

Features and Benefits:

- Very low $V_{CE(sat)}$ 1.5V (typ.)
 - Maximum junction temperature 175°C
 - Short circuit withstand time 3μs
- Trench and field-stop technology for 650V applications offers :
- very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - low V_{CEsat} and positive temperature coefficient
- Low gate charge Q_G
 - Pb-free lead plating; RoHS compliant
 - Very soft, fast recovery anti-parallel Rapid diode
 - Complete product spectrum and PSpice Models:
www.infineon.com/igbt



Potential Applications:

Drives

- GPD (general purpose drives)

Major home appliances

- Air conditioning
- Other major home appliances

Small home appliances

- Other small home appliances

Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
IKA08N65ET6	650V	8A	1.5V	175°C	K08EET6	PG-TO220-3 FP

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